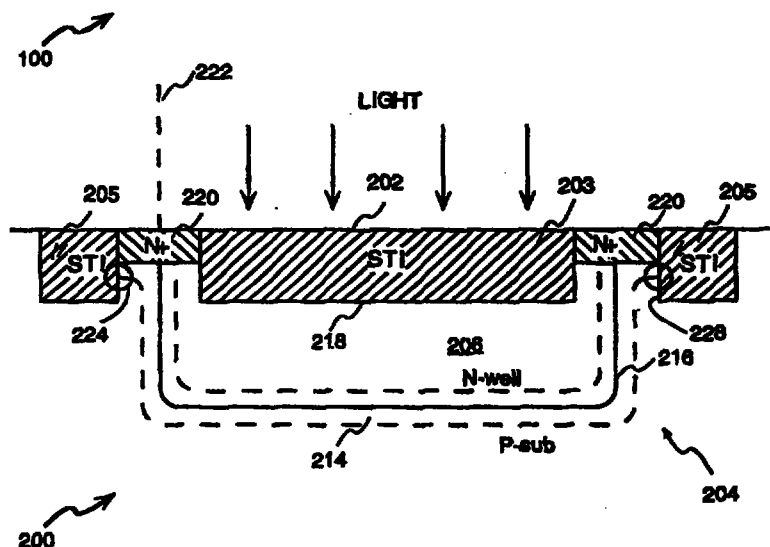




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(57) Abstract

A photodiode (200) is provided. The photodiode (200) includes an insulative region (202) that permits passage of light therethrough. The photodiode (200) also includes a substrate region (204) of a first conductivity type and a well region (206) of a second conductivity type. The well (206) is formed within the substrate (204), beneath the insulative region (202). The well (206) is demarcated from the substrate (204) by a first surface (216). The photodiode (200) further includes a heavily doped region (220) of the second conductivity type. The heavily doped region (220) is formed within the insulative region (202) at a first position (222). The first surface (216) meets the heavily doped region (220) at substantially the first position (222).